

SC12515ZP

**METHOD OF FORMING A BOND PAD****Abstract of the Disclosure**

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A top-most layer (64) is formed over a bond pad layer (62) and under a passivation layer (68) and a polyimide layer (72). Openings (70 and 74) are formed within the passivation layer (68) and the polyimide layer (72) to expose the top-most layer (64), which protects the bond pad layer (62) during the formation of the openings (70 and 74). In one embodiment, the exposed top-most layer (64) is selectively etched using hydrogen peroxide and an amine, such as ammonium hydroxide. Because the chemistry does not attack the bond pad layer (62), the bond pad layer's thickness is not decreased and thus, reliability of the bond pad is maintained.

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(FIG. 1 to accompany abstract)

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